2SC5138

Silicon NPN Epitaxial

HITACHI

ADE-208-225A (Z) 2nd. Edition Mar. 2001

Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product $f_T = 6 \text{ GHz typ}$
- High gain, low noise figure
 PG = 13 dB typ, NF = 1.8 dB typ at f = 900 MHz

Outline

SMPAK



- 1. Emitter
- 2. Base
- 3. Collector

Note: Marking is "YL-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.



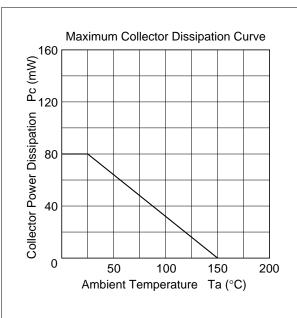
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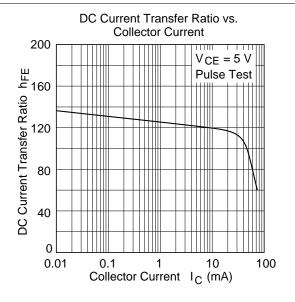
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

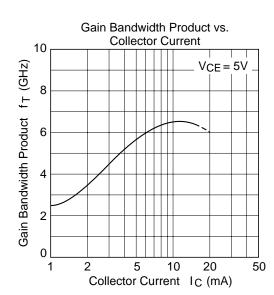
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I _c	30	mA
Collector power dissipation	P _c	80	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

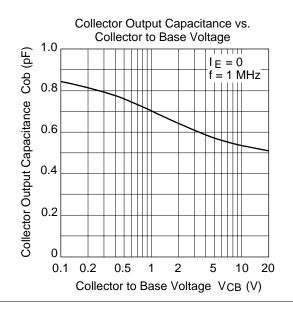
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector cutoff current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	1	mA	V _{CE} = 12 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	0.65	1.05	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0,$ f = 1 MHz
Gain bandwidth product	f⊤	4	6	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$
Power gain	PG	9.5	13	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.8	3.0	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

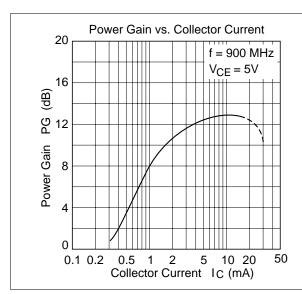


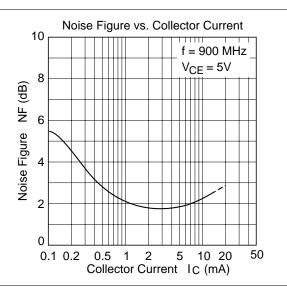




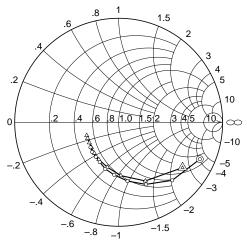


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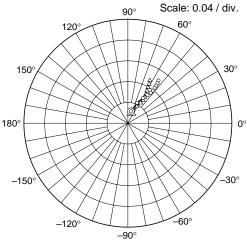
S11 Parameter vs. Frequency



Condition: $V_{CE} = 5 \text{ V}$, $Z_{O} = 50 \Omega$ 100 to 1000 MHz (100 MHz step) \bigcirc (IC = 5 mA)

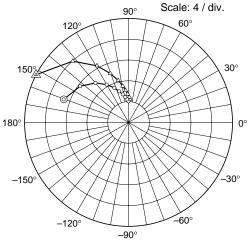
 $\underline{\hspace{1cm}}$ (I C = 10 mA)

S12 Parameter vs. Frequency



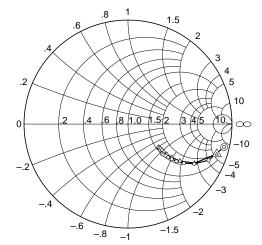
Condition: $\,\text{V}_{\text{CE}}\text{=}\,5\,\,\text{V}$, Zo = 50 Ω 100 to 1000 MHz (100 MHz step) ⊚——o (I_C = 5 mA) (IC = 10 mA)

S21 Parameter vs. Frequency



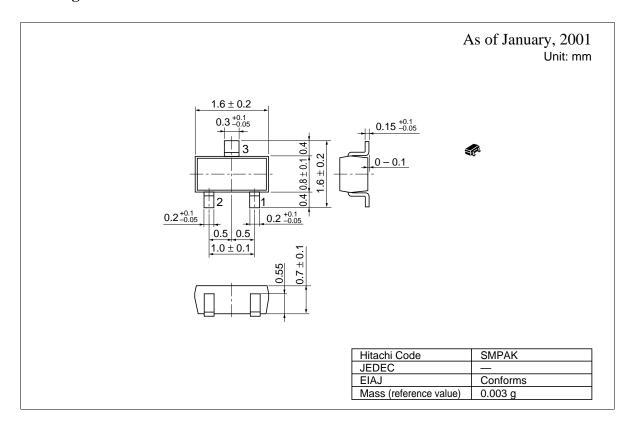
Condition: $V_{CE} = 5 \text{ V}$, $Z_{O} = 50 \Omega$ 100 to 1000 MHz (100 MHz step) \bigcirc (IC = 5 mA) $\underline{\hspace{1cm}}$ (I C = 10 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω 100 to 1000 MHz (100 MHz step) ⊚——o (I_C = 5 mA) (IC = 10 mA)<u>A</u>-

Package Dimensions



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